

2 Electrical Specifications

This section shows the electrical specifications for the APT75DQ60BG device.

2.1 Absolute Maximum Ratings

The following table lists the absolute maximum ratings for the APT75DQ60BG device.

All ratings: $T_c = 25^\circ\text{C}$ unless otherwise specified.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_R	Maximum DC reverse voltage	600	V
V_{RRM}	Maximum peak repetitive reverse voltage	600	
V_{RWM}	Maximum working peak reverse voltage	600	
$I_{F(AV)}$	Maximum average forward current ($T_c = 108^\circ\text{C}$, duty cycle = 0.5)	75	A
$I_{F(RMS)}$	RMS forward current	117	
I_{FSM}	Non-repetitive forward surge current ($T_J = 45^\circ\text{C}$, 8.3 ms)	600	
E_{AVL}	Avalanche energy (1 A, 40 mH)	20	mJ
T_J, T_{STG}	Operating and storage temperature range	-55 to 175	$^\circ\text{C}$
T_L	Lead temperature for 10 seconds	300	

The following table shows the thermal and mechanical characteristics of the APT75DQ60BG device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance			0.34	$^\circ\text{C}/\text{W}$
W_t	Package weight		0.22		oz
			6.2		g
	Maximum mounting torque			10	lbf•in
				1.1	N•m

2.2 Electrical Performance

The following table lists the static characteristics of the APT75DQ60BG device.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Forward voltage	$I_F = 75\text{ A}$		2.0	2.5	V
		$I_F = 150\text{ A}$		2.4		
		$I_F = 75\text{ A}, T_J = 125^\circ\text{C}$		1.7		
I_{RM}	Maximum reverse leakage current	$V_R = 600\text{ V}$			25	μA
		$V_R = 600\text{ V}, T_J = 125^\circ\text{C}$			500	
C_J	Junction capacitance	$V_R = 200\text{ V}$		110		pF

2.3 Dynamic Characteristics

The following table lists the dynamic characteristics of the APT75DQ60BG device.

Table 4 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_{rr}	Reverse recovery time	$I_F = 1\text{ A}$ $di_F/dt = -100\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$ $T_J = 25\text{ }^\circ\text{C}$		29		ns
t_{rr}	Reverse recovery time	$I_F = 75\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$		31		
Q_{rr}	Reverse recovery charge	$V_R = 400\text{ V}$ $T_C = 25\text{ }^\circ\text{C}$		55		nC
I_{RRM}	Maximum reverse recovery current	$T_C = 25\text{ }^\circ\text{C}$		4		A
t_{rr}	Reverse recovery time	$I_F = 75\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$		140		ns
Q_{rr}	Reverse recovery charge	$V_R = 400\text{ V}$ $T_C = 125\text{ }^\circ\text{C}$		650		nC
I_{RRM}	Maximum reverse recovery current	$T_C = 125\text{ }^\circ\text{C}$		9		A
t_{rr}	Reverse recovery time	$I_F = 75\text{ A}$ $di_F/dt = -1000\text{ A}/\mu\text{s}$		90		ns
Q_{rr}	Reverse recovery charge	$V_R = 400\text{ V}$ $T_C = 125\text{ }^\circ\text{C}$		1300		nC
I_{RRM}	Maximum reverse recovery current	$T_C = 125\text{ }^\circ\text{C}$		27		A

2.4 Typical Performance Curves

This section shows the typical performance curves for the APT75DQ60BG device.

Figure 1 • Maximum Transient Thermal Impedance

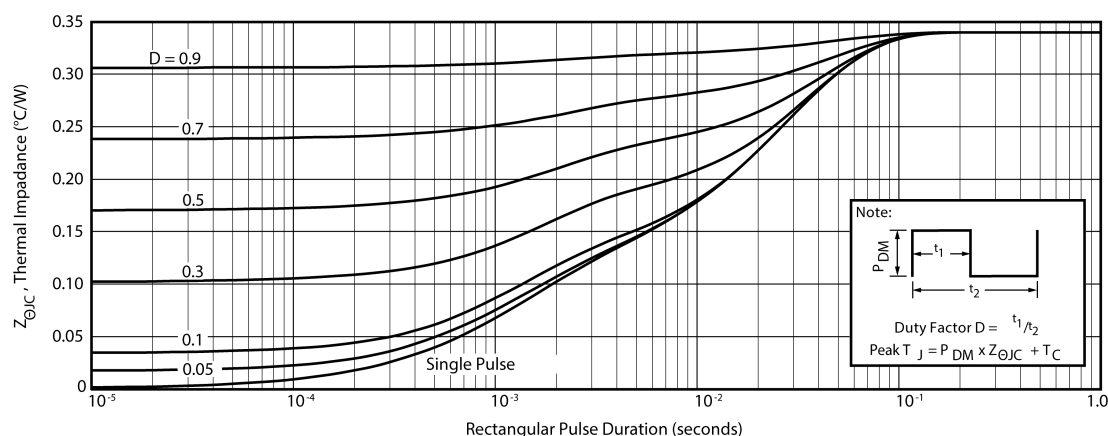


Figure 2 • Forward Current vs. Forward Voltage

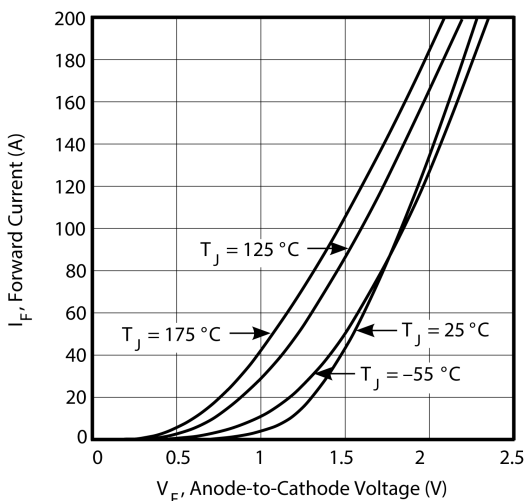


Figure 3 • RRT vs. Current Rate of Change

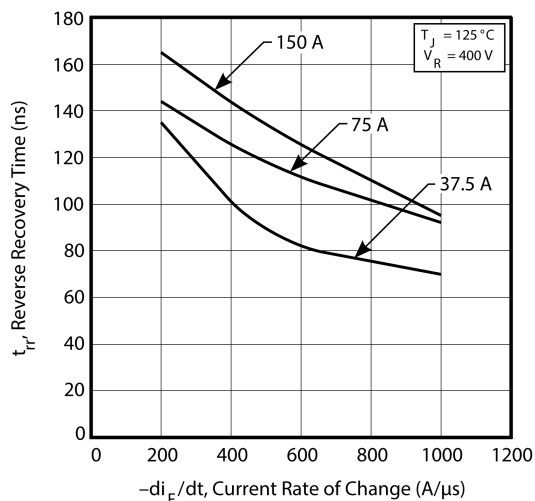


Figure 4 • Reverse Recovery Charge vs. Current Rate of Change

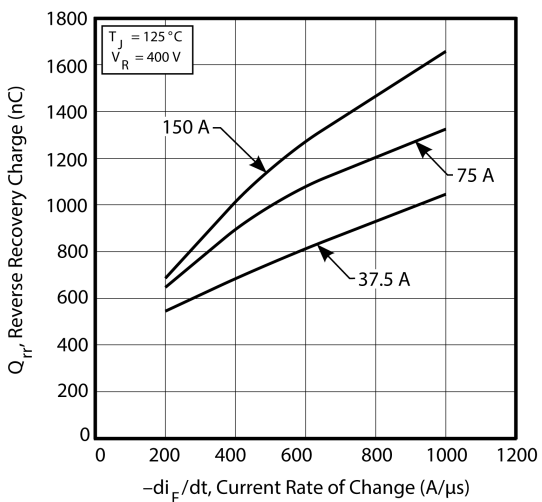


Figure 5 • Reverse Recovery Current vs. Current Rate of Change

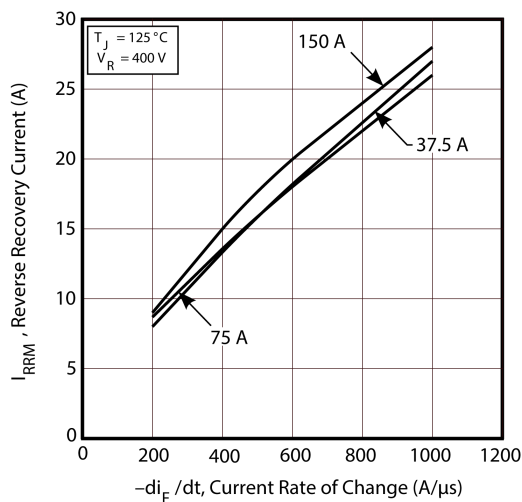


Figure 6 • Dynamic Parameters vs. Junction Temperature

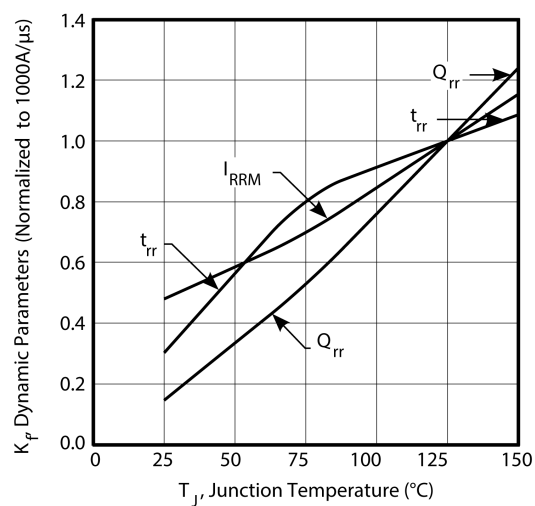


Figure 7 • Maximum Average Forward Current vs. Case Temperature

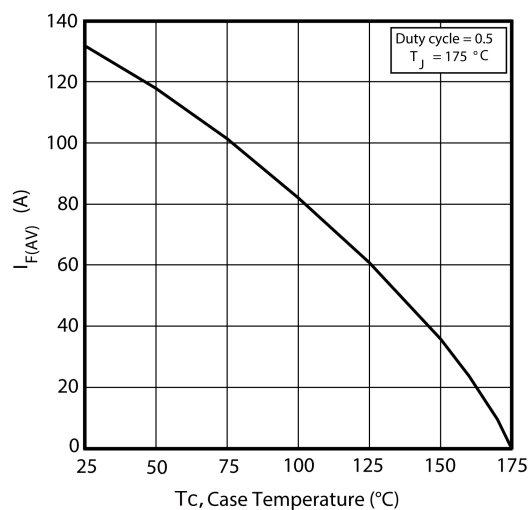
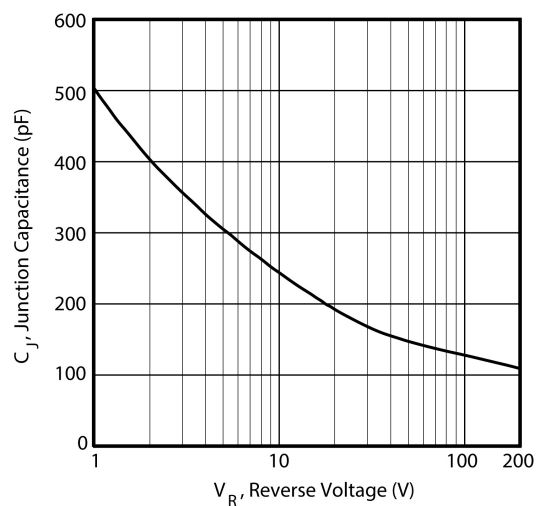


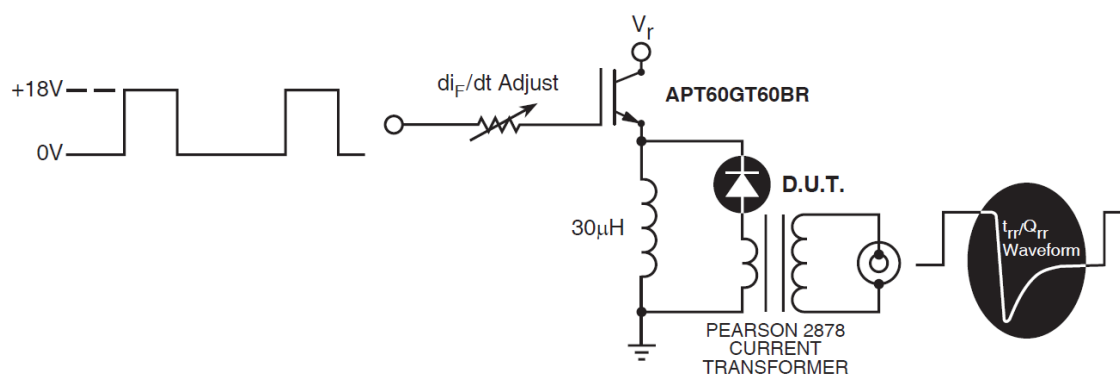
Figure 8 • Junction Capacitance vs. Reverse Voltage



2.5 Reverse Recovery Overview

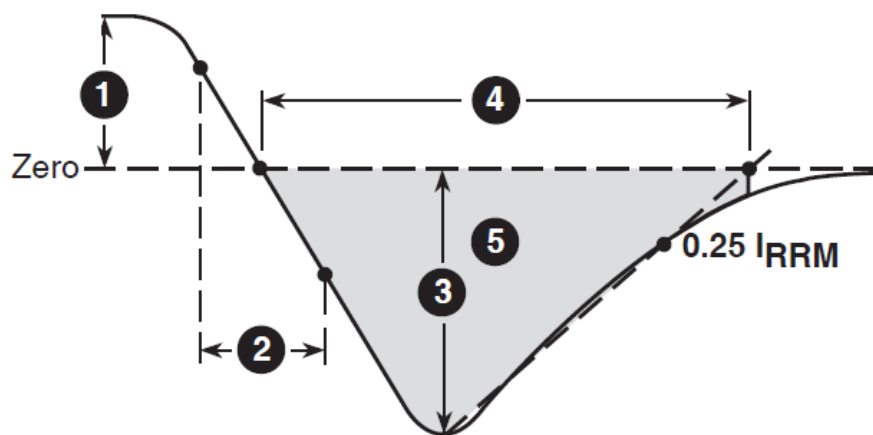
The following figure illustrates the diode test circuit for the APT75DQ60BG device.

Figure 9 • Diode Test Circuit



The following figure illustrates the diode reverse recovery waveform and definitions for the APT75DQ60BG device.

Figure 10 • Diode Reverse Recovery Waveform and Definitions



1. I_F —Forward conduction current.
2. di_F/dt —Rate of diode current change through zero crossing.
3. I_{RRM} —Maximum reverse recovery current.
4. t_{rr} —Reverse recovery time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
5. Q_{rr} —Area under the curve defined by I_{RRM} and t_{rr} .

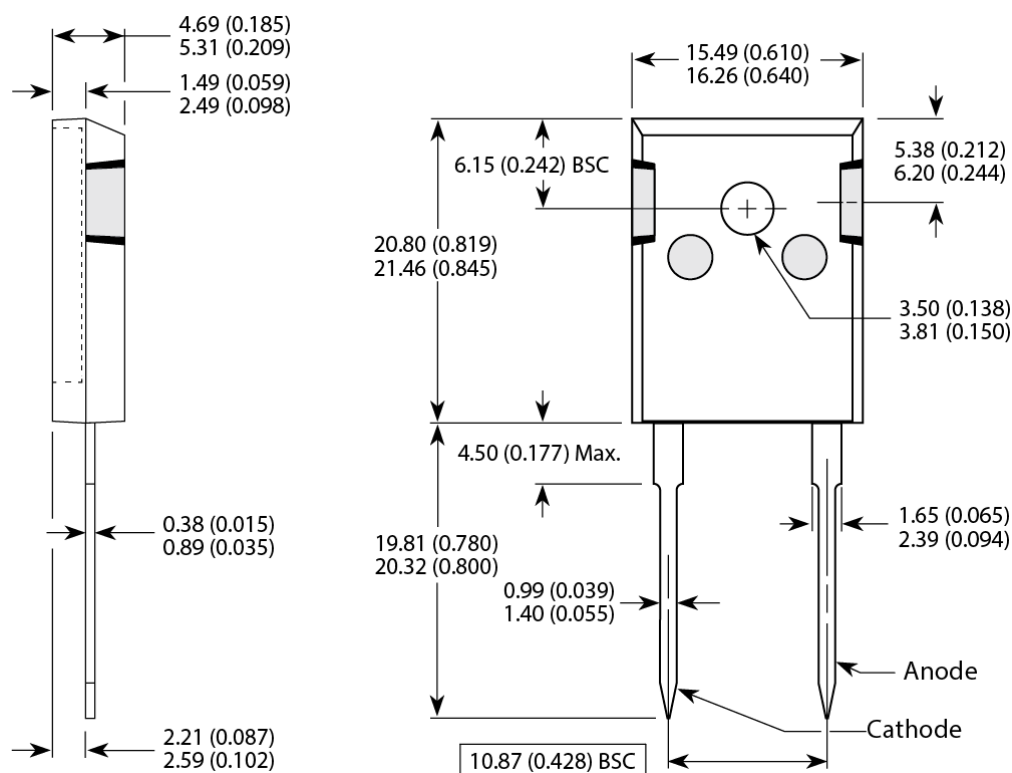
3 Package Specification

This section shows the package specification for the APT75DQ60BG device.

3.1 Package Outline Drawing

The following figure illustrates the TO-247 package outline of the APT75DQ60BG device. Dimensions are in millimeters and (inches).

Figure 11 • Package Outline Drawing



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